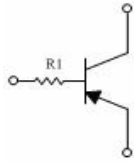


## Small Signal Diode

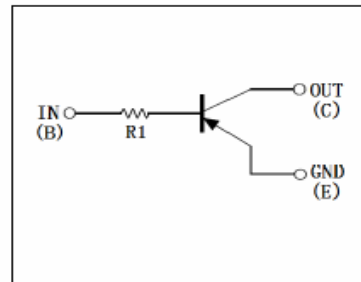


## DTA114 TM/TE/TUA/TCA/TSA PNP Digital Transistor

### Features

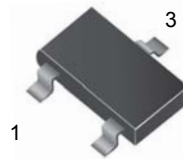
- ◇ Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistor (see equivalent circuit).
- ◇ The bias resistors consist of thin -film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- ◇ Only the on/off conditions need to be set for operation, marking device design easy.
- ◇ Green compound (Halogen free) with suffix "G" on packing code and prefix "G" on date code.

### • Equivalent Circuit



### Ordering Information

Package	Part No.	Packing	Marking
SOT-723	DTA114 TM	8K / 7" Reel	94
SOT-523	DTA114 TE	3K / 7" Reel	94
SOT-323	DTA114 TUA	3K / 7" Reel	94
SOT-23	DTA114 TCA	3K / 7" Reel	94
TO-92S	DTA114 TSA	3K / 7" Reel	



### SOT-723/SOT-523 SOT-323/SOT-23

- 1.IN
- 2.GND
- 3.OUT



### TO-92S

- 1.GND
- 2.OUT
- 3.IN

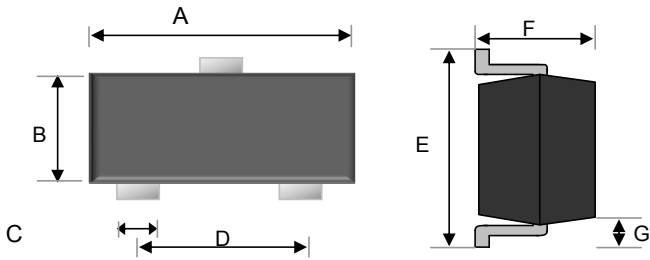
### Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

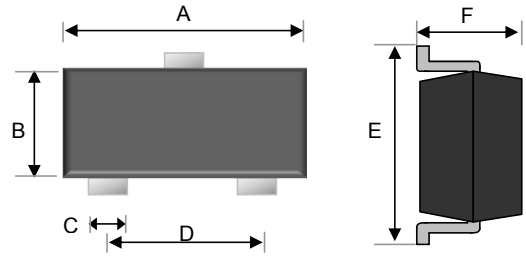
Type Number	Symbol	Value					Units
		TM	TE	TUA	TCA	TSA	
Power Dissipation	PD	100	150	200		300	mW
Collector-Emitter Voltage	$V_{CBO}$	-50					V
Emitter-Base Voltage	$V_{CEO}$	-50					V
Emitter-Base Voltage	$V_{EBO}$	-5					
Collector Current	$I_C$	-100					mA
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to + 150					°C

Notes:1. Valid provided that electrodes are kept at ambient temperature

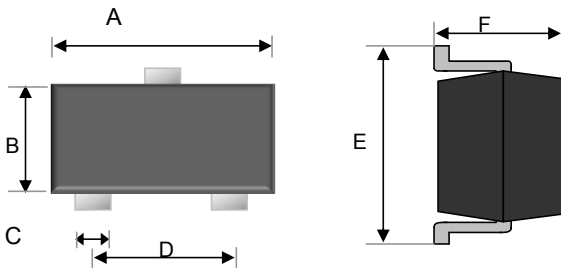
Parameter	Symbol	Min	Typ	Max	Condition	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	-50			$I_C = -50\mu A, I_E = 0$	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-50			$I_C = -1mA, I_B = 0$	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-5			$I_E = -50\mu A, I_C = 0$	V
Collector cut-off current	$I_{CBO}$			-0.5	$V_{CB} = -50V, I_E = 0$	$\mu A$
Emitter cut-off current	$I_{EBO}$			-0.5	$V_{EB} = -4V, I_C = 0$	$\mu A$
DC Current Gain	$V_{CE(sat)}$			-0.3	$I_C = -10mA, I_B = -1mA$	V
Input Resistance	$h_{FE}$	100	250	600	$V_{CE} = -5V, I_C = -1mA$	
Resistance Ratio	$R_1$	7	10	13		K $\Omega$
Transition Frequency	$f_T$		250		$V_{CE} = -10V, I_E = -5mA, f = 100MHz$	MHz

**DTA114 TM/TE/TUA/TCA/TSA**  
**PNP Digital Transistor**
**SOT-23**


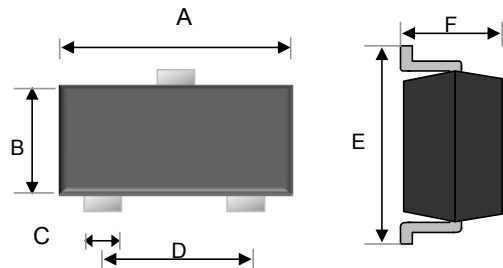
Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	2.80	3.00	0.11	0.12
B	1.20	1.40	0.05	0.06
C	0.30	0.50	0.01	0.02
D	1.80	2.00	0.07	0.08
E	2.25	2.55	0.09	0.10
F	0.90	1.20	0.04	0.04
G	0.550 REF		0.022 REF	

**SOT-323**


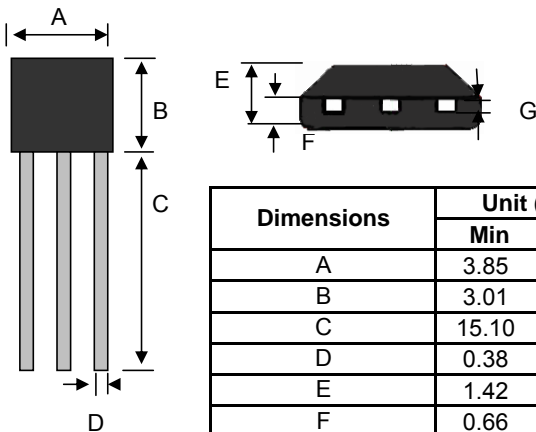
Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	1.90	2.10	0.07	0.08
B	1.15	1.35	0.05	0.05
C	0.25	0.35	0.01	0.01
D	1.20	1.40	0.05	0.06
E	2.00	2.20	0.08	0.09
F	0.80	1.00	0.03	0.04

**SOT-523**


Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	1.50	1.70	0.06	0.07
B	0.70	0.80	0.03	0.03
C	0.25	0.35	0.01	0.01
D	0.90	1.10	0.04	0.04
E	1.50	1.70	0.06	0.07
F	0.70	0.90	0.03	0.04

**SOT-723**


Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	1.15	1.25	0.05	0.05
B	0.75	0.85	0.03	0.03
C	0.17	0.27	0.01	0.01
D	0.8 TYP		0.31 TYP	
E	1.15	1.25	0.05	0.05
F		0.50		0.02

**TO-92S**


Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	3.85	4.15	0.15	0.16
B	3.01	3.31	0.12	0.13
C	15.10	15.50	0.59	0.61
D	0.38	0.55	0.01	0.02
E	1.42	1.62	0.06	0.06
F	0.66	0.86	0.03	0.03
G	0.36	0.51	0.01	0.02